



OMB No. 0651-0011 Page 1 of 1

INFORMATION		Atty. Docket No.: 150.00800102		Serial No.: 09/651,702			
DISC	CLOSURE					_	
STA	TEMENT	Applicant(s): B	Brian A. VAARTSTR	RA			
		Filing Date: August 30, 2000		Group: 1756			
	#4						
	<i>1</i>	J.S. PATENT	DOCUMENTS	· · · · · · · · · · · · · · · · · · ·			
Examiner Initial	Document Number	Date	Name	Class	SubClass	Filing Date I Appropriate	
NB	4,296,146	10/20/81	Penn	427	38		
	4,778,536	10/18/88	Grebinski	134	34		
	4,861,424	08/29/89	Fujimura et al.	156	to #3		
	4,944,837	07/31/90	Nishikawa et al.	BC	6-190	\	
	5,013,366	05/07/91	Jackson et al.	#36H	2	2	
	5,037,506	08/06/91	Gupta et al.	图56	6296		
	5,298,112	03/29/94	Hayasaka et al.	13%	446		
	5,382,316	01/17/95	Hills et al.	1500	MARY 3		
	5,401,322	03/28/95	Marshall	134	13		
	5,403,436	04/04/95	Fujimura et al.	150	443		
	5,643,474	7/1/97	Sangeeta	216	96		
	5,651,860	07/29/97	Li	154	659.11		
	6,024,801	02/15/00	Wallace et al.	134	1 8		
n B	6,149,828	11/20/00	Vaartstra	216	57 g	င်း 🗓	
	FOE	REIGN PATE	NT DOCUMENTS		20	<u> </u>	
	Document Number	Date	Country	Class	SubClass	Translation Yes No	
nh	WO 95/20476	08/03/95	PCT				
	HER DOCUMENTS		***************************************				
ng	Water at Elevated 3940-3944 (1995)	G. Bakker et al., "Removal of Thermally Grown Silicon Dioxide Films Using Water at Elevated Temperature and Pressure", <u>J. Electrochem. Soc.</u> , <u>142</u> (11), 3940-3944 (1995).					
M	Semiconductor In	M. Dax, "Removing Photoresist Without Plasmas or Liquid Strippers," <u>Semiconductor International: Contamination Control News</u> , 52 (September 1996).					
M	Technology, 73-7	Deal et al., "Vapor Phase Wafer Cleaning: Processing for the 1990s," Solid State Technology, 73-77 (July 1990).					
M	Geologists", <u>45(</u> 7	T. Nolan, "Economic Geology and the Bulletin of the Society of Economic Geologists", 45(7), Title Page, Table of Contents, pgs. 601, 629-653 (1950).					
EXÁMINE	_		Date Considered	,			
Michelaneer			2/21/02				
	ial if citation considered, whethe						